

STD18NF03L

N-channel 30V - 0.038Ω - 17A - DPAK STripFET™ II Power MOSFET

Features

Туре	V _{DSS}	R _{DS(on)}	I _D
STD18NF03L	30V	<0.05Ω	17A

- Exceptional dv/dt capability
- Low gate charge at 100°C
- Application oriented characterization
- 100% avalanche tested

Description

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size" strip-based process. The resulting transistor shows extremely high packing density for low onresistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Application

- Switching applications
 - Automotive

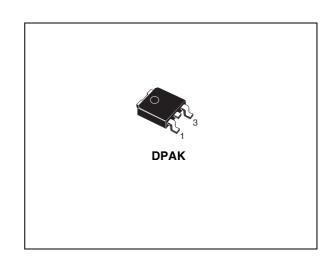


Figure 1. Internal schematic diagram

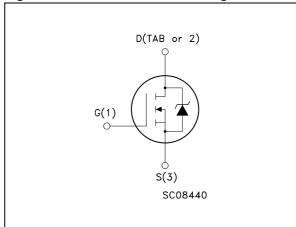


Table 1. Device summary

Order code	Marking	Package	Packaging	
STD18NF03L	D18NF03L	DPAK	Tape & reel	

Contents STD18NF03L

Contents

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STD18NF03L Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V _{DS}	Drain-source voltage (V _{GS} = 0)	30	V	
V _{GS}	Gate- source voltage	± 16	V	
I _D	Drain current (continuous) at T _C = 25°C	17	Α	
I _D	Drain current (continuous) at T _C = 100°C	12	Α	
I _{DM} ⁽¹⁾	Drain current (pulsed)	68	Α	
P _{tot}	Total dissipation at T _C = 25°C	30	W	
	Derating Factor	0.2	W/°C	
dv/dt ⁽²⁾	Peak diode recovery avalanche energy	7	V/ns	
E _{AS} (3)	Single pulse avalanche energy	200	mJ	
T _{stg}	Storage temperature			
T _j	Max. operating junction temperature			

^{1.} Pulse width limited by safe operating area.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case max	5.0	°C/W
Rthj-amb	Thermal resistance junction-to ambient max	100	°C/W
TJ	Maximum lead temperature for soldering purpose	275	°C

^{2.} $I_{SD} \le 7A$, di/dt $\le 300A/\mu s$, $V_{DD} = V_{(BR)DSS}$, $T_j \le T_{JMAX}$

^{3.} Starting $T_j = 25$ °C, $I_D = 8.5$ A, $V_{DD} = 15$ V

Electrical characteristics STD18NF03L

2 Electrical characteristics

(T_{CASE} =25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	30			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.5	2.2	V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10V, I_D = 8.5A$ $V_{GS} = 5V, I_D = 8.5A$		0.038 0.045	0.05 0.06	Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} (1)	Forward transconductance	$V_{DS} > I_{D(on)} x$ $R_{DS(on)max}$, $I_D = 8.5A$		12		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		320 155 28		pF pF pF
$\begin{array}{c} t_{\text{d(on)}} \\ t_{\text{r}} \\ t_{\text{d(off)}} \\ t_{\text{f}} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 15V, I_D = 8.5A R_G = 4.7 Ω V_{GS} = 5V (see <i>Figure 14</i>)		11 100 25 22		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 3024V, I_{D} = 17A,$ $V_{GS} = 5V, R_{G} = 4.7\Omega$ (see <i>Figure 15</i>)		4.8 2.25 1.7	6.5	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%.

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				22 88	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 17A, V _{GS} = 0			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 17A$, di/dt = 100A/ μ s, $V_{DD} = 15V$, $T_{j} = 150$ °C (see <i>Figure 16</i>)		28 18 1.3		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

Electrical characteristics STD18NF03L

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

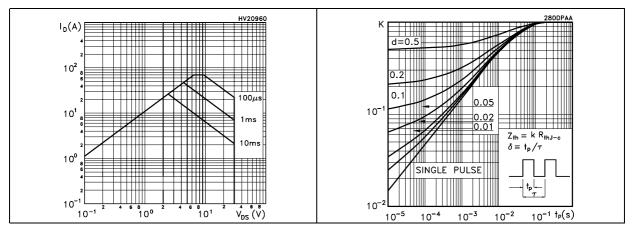


Figure 4. Output characteristics

Figure 5. Transfer characteristics

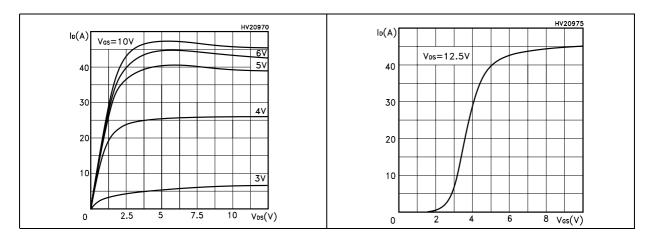


Figure 6. Transconductance

Figure 7. Static drain-source on resistance

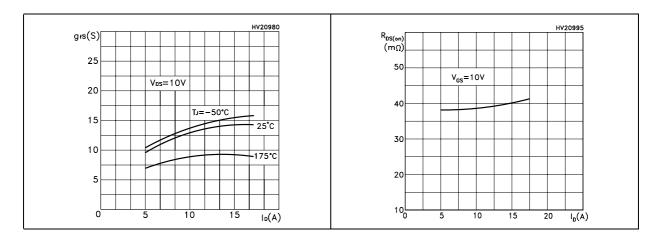


Figure 8. Gate charge vs. gate-source voltage Figure 9. Capacitance variations

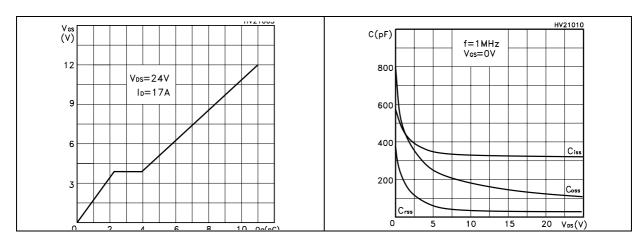


Figure 10. Normalized gate threshold voltage vs. temperature

Figure 11. Normalized on resistance vs. temperature

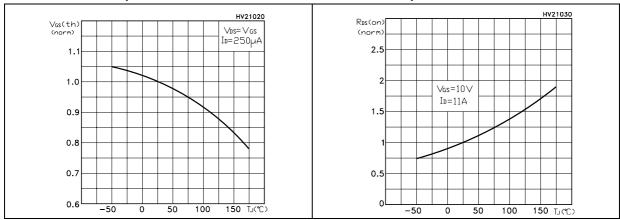
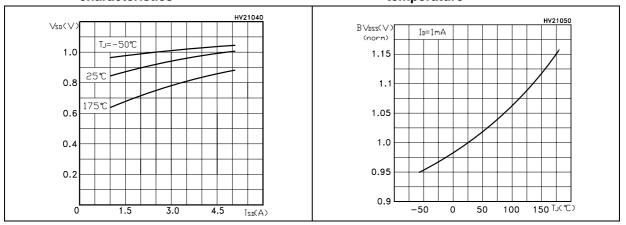


Figure 12. Source-drain diode forward characteristics

Figure 13. Normalized breakdown voltage vs. temperature



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Test circuit STD18NF03L

3 Test circuit

Figure 14. Switching times test circuit for resistive load

Figure 15. Gate charge test circuit

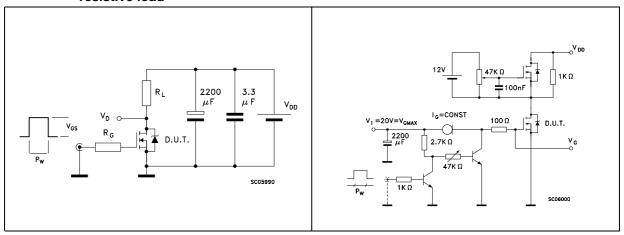


Figure 16. Test circuit for inductive load switching and diode recovery times

Figure 17. Unclamped Inductive load test circuit

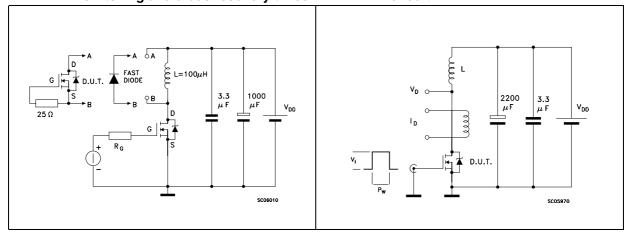
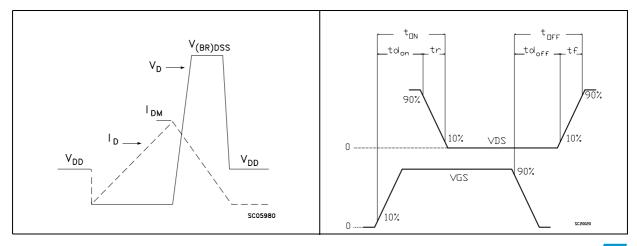


Figure 18. Unclamped inductive waveform

Figure 19. Switching time waveform



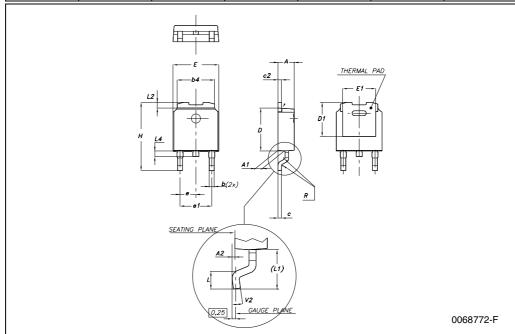
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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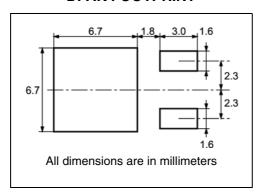
DPAK MECHANICAL DATA

DIM		mm.			inch	inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α	2.2		2.4	0.086		0.094	
A1	0.9		1.1	0.035		0.043	
A2	0.03		0.23	0.001		0.009	
В	0.64		0.9	0.025		0.035	
b4	5.2		5.4	0.204		0.212	
С	0.45		0.6	0.017		0.023	
C2	0.48		0.6	0.019		0.023	
D	6		6.2	0.236		0.244	
D1		5.1			0.200		
E	6.4		6.6	0.252		0.260	
E1		4.7			0.185		
е		2.28			0.090		
e1	4.4		4.6	0.173		0.181	
Н	9.35		10.1	0.368		0.397	
L	1			0.039			
(L1)		2.8			0.110		
L2		0.8			0.031		
L4	0.6		1	0.023		0.039	
R		0.2			0.008		
V2	0°		8°	0°		8°	

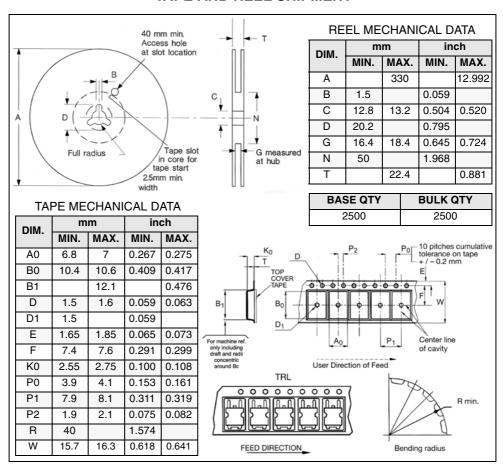


5 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



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Revision history STD18NF03L

6 Revision history

Table 7. Revision history

Date	Revision	Changes
27-Jul-2007	1	First release

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